

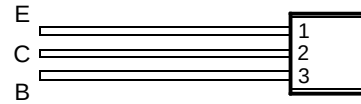
TIPP32, TIPP32A, TIPP32B, TIPP32C PNP SILICON POWER TRANSISTORS

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MAY 1989 - REVISED MARCH 1997

- 20 W Pulsed Power Dissipation
- 100 V Capability
- 2 A Continuous Collector Current
- 4 A Peak Collector Current
- Customer-Specified Selections Available

LP PACKAGE
(TOP VIEW)



MDTRAB

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIPP32	V_{CBO}	-40	V
	TIPP32A		-60	
	TIPP32B		-80	
	TIPP32C		-100	
Collector-emitter voltage ($I_B = 0$)	TIPP32	V_{CEO}	-40	V
	TIPP32A		-60	
	TIPP32B		-80	
	TIPP32C		-100	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-2	A
Peak collector current (see Note 1)		I_{CM}	-4	A
Continuous base current		I_B	-1	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	0.8	W
Pulsed power dissipation (see Note 3)		P_T	20	W
Operating junction temperature range		T_j	-55 to +150	°C
Storage temperature range		T_{stg}	-55 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 6.4 mW/°C.
 3. $V_{CE} = 20$ V, $I_C = 1$ A, $t_p = 10$ ms, duty cycle $\leq 2\%$.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



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electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -5 \text{ mA}$ (see Note 4)	$I_B = 0$	TIPP32 TIPP32A TIPP32B TIPP32C	-40 -60 -80 -100			V
I_{CES} Collector-emitter cut-off current	$V_{CE} = -40 \text{ V}$ $V_{CE} = -60 \text{ V}$ $V_{CE} = -80 \text{ V}$ $V_{CE} = -100 \text{ V}$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIPP32 TIPP32A TIPP32B TIPP32C			-0.2 -0.2 -0.2 -0.2	mA
I_{CEO} Collector cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$	TIPP32/32A TIPP32B/32C			-0.3 -0.3	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-1	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -4 \text{ V}$ $V_{CE} = -4 \text{ V}$	$I_C = -1 \text{ A}$ $I_C = -2 \text{ A}$	(see Notes 4 and 5)	20 10			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -375 \text{ mA}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-1	V
V_{BE} Base-emitter voltage	$V_{CE} = -4 \text{ V}$	$I_C = -2 \text{ A}$	(see Notes 4 and 5)			-1.5	V
h_{fe} Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ kHz}$	20			
$ h_{fe} $ Small signal forward current transfer ratio	$V_{CE} = -10 \text{ V}$	$I_C = -0.5 \text{ A}$	$f = 1 \text{ MHz}$	3			

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

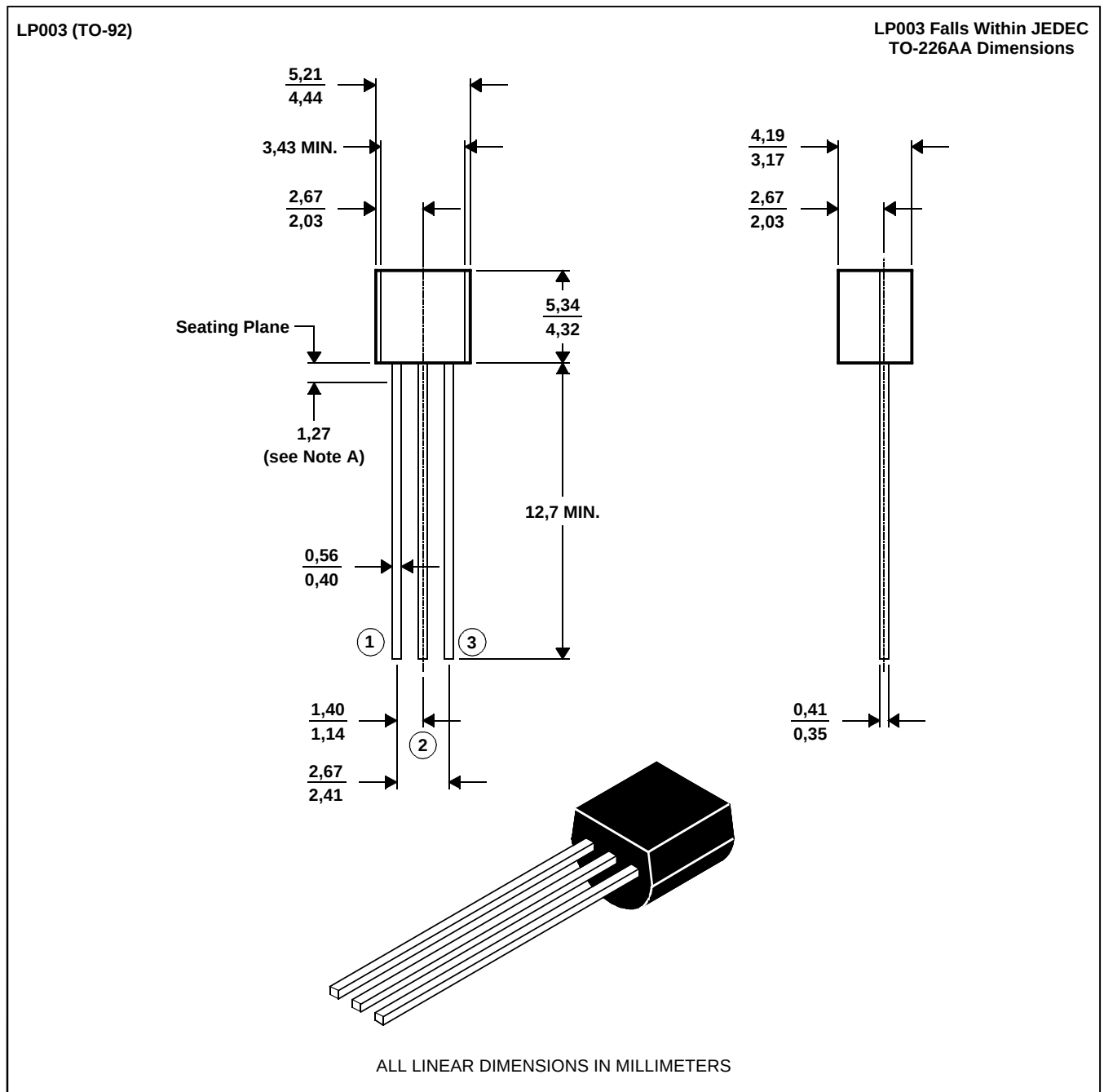
PRODUCT INFORMATION

MECHANICAL DATA

LP003 (TO-92)

3-pin cylindrical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: Lead dimensions are not controlled in this area.

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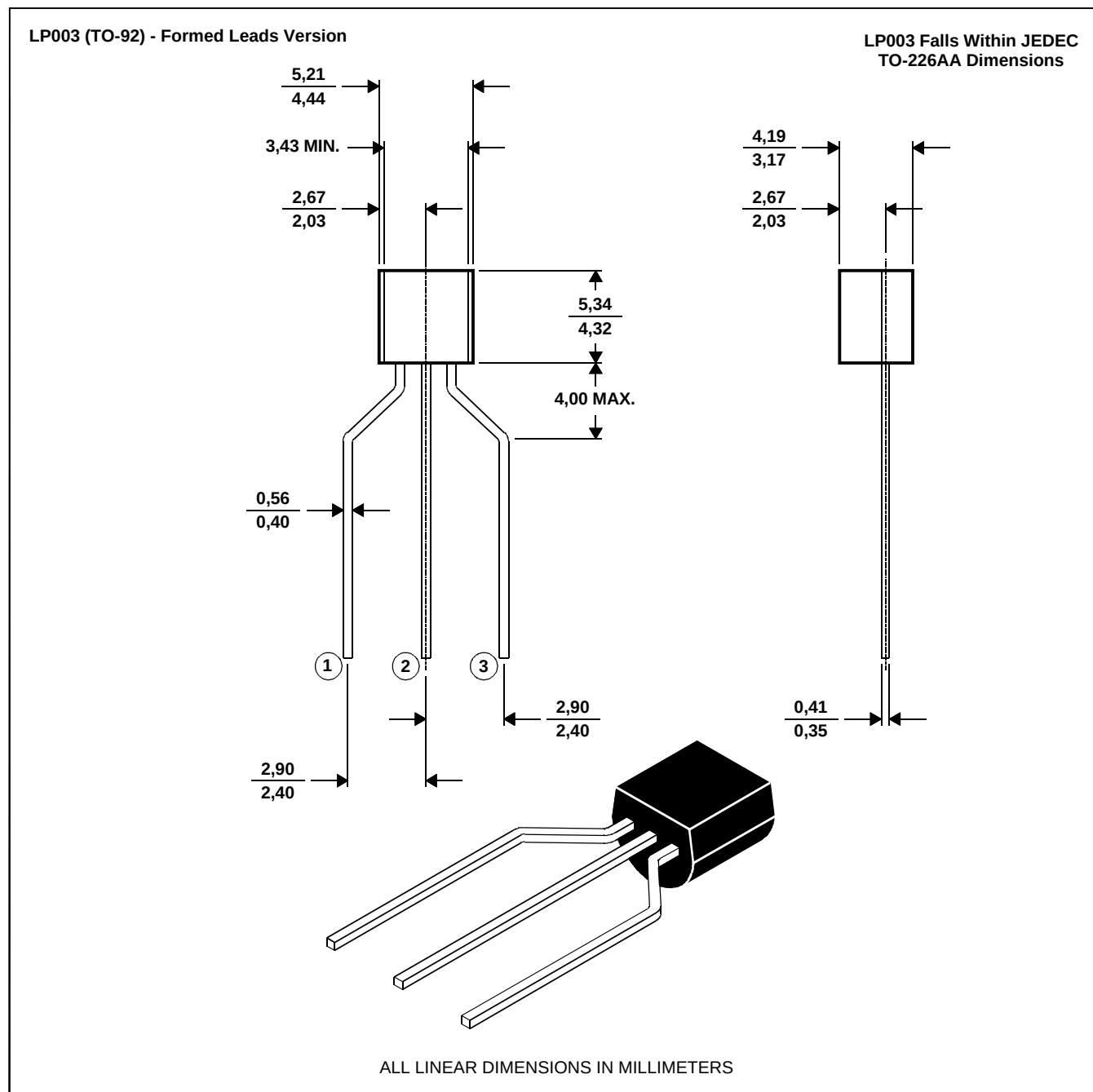
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MDXXAR

PRODUCT INFORMATION

LPR
tape dimensions

Technical drawing of a roof structure, showing two elevations and a plan view.

Elevation 1 (Left):

- Top width: $\frac{5,21}{4,44}$
- Height from top to first step: 3,43 MIN.
- Height from first step to second step: $\frac{2,67}{2,03}$
- Width of second step: $\frac{5,34}{4,32}$
- Height from second step to third step: 4,00 MAX.
- Width of third step: $\frac{0,56}{0,40}$

Elevation 2 (Right):

- Top width: $\frac{4,19}{3,17}$
- Height from top to first step: $\frac{2,67}{2,03}$
- Width of first step: $\frac{0,41}{0,35}$

Plan View (Bottom):

- Overall width: $\frac{32,00}{23,00}$
- Width of first section: $\frac{27,68}{17,66}$
- Width of second section: $\frac{16,50}{15,50}$
- Width of third section: $\frac{11,00}{8,50}$
- Width of fourth section: $\frac{9,75}{8,50}$
- Width of fifth section: $\frac{19,00}{5,50}$
- Width of sixth section: $\frac{0,50}{0,00}$
- Overall length: $\frac{19,00}{17,50}$
- Length of first section: $\frac{13,70}{11,70}$
- Length of second section: $\frac{2,90}{2,40}$
- Length of third section: $\frac{6,75}{5,95}$
- Length of fourth section: $\frac{13,00}{12,40}$
- Length of fifth section: $\frac{2,90}{2,40}$
- Length of sixth section: $\frac{4,30}{3,70}$
- Minimum distance between sections: 2,50 MIN.

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